

10048192 10/048192
Rec'd PCT/PTO 25 JAN 2002
Attn: Docket No.: 12816-042001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Engelhardt, M., et al. Art Unit : Unknown
Serial No. : To Be Assigned Examiner : Unknown
Filed : Herewith
Title : METHOD FOR PRODUCING A SEMICONDUCTOR MEMORY ELEMENT

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Prior to examination, please amend the application as follows:

In the claims:

Amend claims 1-6 as follows:

1. (Once amended) A method for fabricating a contact hole for a semiconductor memory component, having a silicon substrate, an intermediate dielectric layer arranged on said substrate, and an upper layer arranged on said intermediate dielectric layer, the method comprising:

forming a perforated mask on the upper layer, the mask including a material which exhibits temperature stability during a later deposition process;

etching the upper layer and a depression into the intermediate dielectric layer as far as a residual thickness using the perforated mask;

depositing a layer including O₃/TEOS-SiO₂ onto a structure thus obtained including the perforated mask;

removing the layer including O₃/TEOS-SiO₂ from a bottom of the depression by etching; and

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